



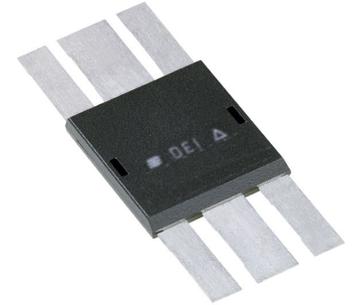
Silicon Carbide Schottky Diode

V_{RRM} = 600 V

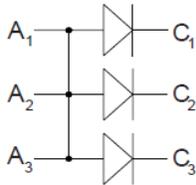
I_{F(AVG)} = 10 A

C_J = 80 pF

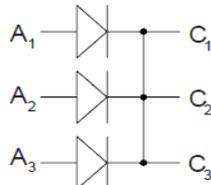
Part Number	V _{RRM} (V)	I _{F(AVG)} (A)	Configuration
SS150TA60110	600	10	Triple Common Anode
SS150TC60110	600	10	Triple Common Cathode
SS150TI60110	600	10	Triple Independent



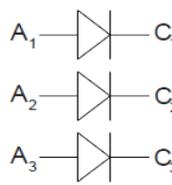
Triple Anode (TA)



Triple Cathode (TC)



Triple Independent (TI)



A = Anode C = Cathode

Symbol	Parameter	Test Conditions	Maximum Ratings
V _{RRM}	Repetitive Peak Reverse Voltage		600 V
V _{RSM}	Repetitive Surge Reverse Voltage		600 V
V _{DC}	DC Blocking Voltage		600 V
I _{F(AVG)}	Average Forward Current	T _J = 175°C	10 A
I _{FRM}	Repetitive Peak Forward Surge Current	T _{VJ} = 45°C, t _p = 10 ms Half Sine Wave D = 0.3	25 A
T _{VJ}	Operating Virtual Junction Temperature		-55 to +175 °C
T _{STG}	Storage Temperature		-55 to +175 °C
P _{TOT}	T _C = 25 °C (20 W/device)		60 W

Features

- 600 V SiC Schottky Diode
- Surface Mount Package
- Zero Reverse Recovery
- Zero Forward Recovery
- High Frequency Operation
- Temperature Independent Behavior
- Positive Temperature Coefficient for V_F

Applications

- MHz Switch Mode Power Supplies
- High Frequency Converters
- Resonant Converters
- Rectifier Circuits

Symbol	Parameter	Test Conditions	Characteristic Values		
			Typ.	Max.	Units
T _J = 25°C unless otherwise specified					
V _F	Forward Voltage	I _F = 5 A, T _J = 25°C T _J = 175°C	1.6 2	1.8 2.4	V
I _R	Reverse Current	V _R = 600 V, T _J = 25°C T _J = 175°C	10 20	50 200	µA
C _J	Junction Capacitance	f = 1 MHz, V _R = 0 V V _R = 200 V V _R = 600 V	485 85 80		pF
R _{THJC}	Thermal Resistance		2.5		°C/W
T _L	Lead Soldering Temperature	1.6 mm (0.063 in) from case for 10 s	300		°C
Isolation	Pin to Substrate Pin to Pin		>1800 >1500		V _{RMS}
Weight			2		g

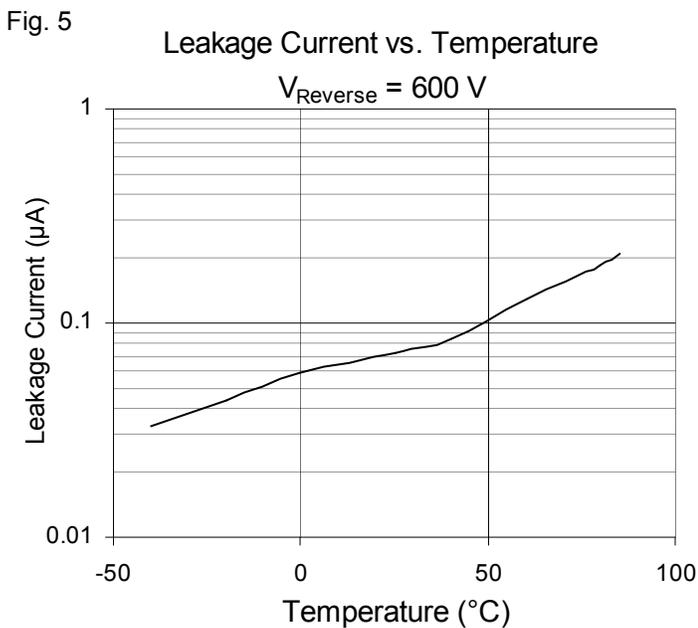
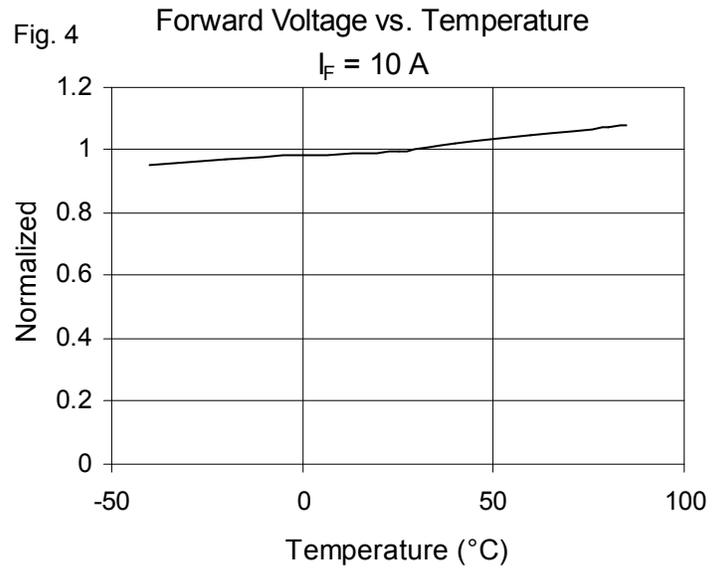
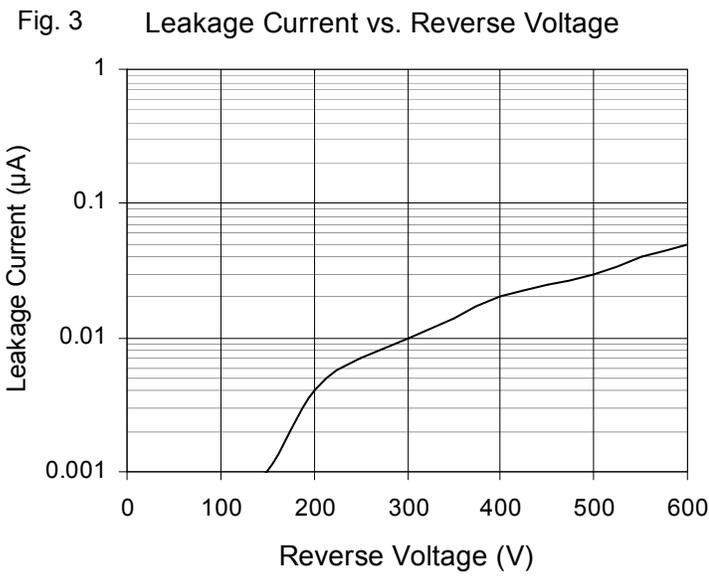
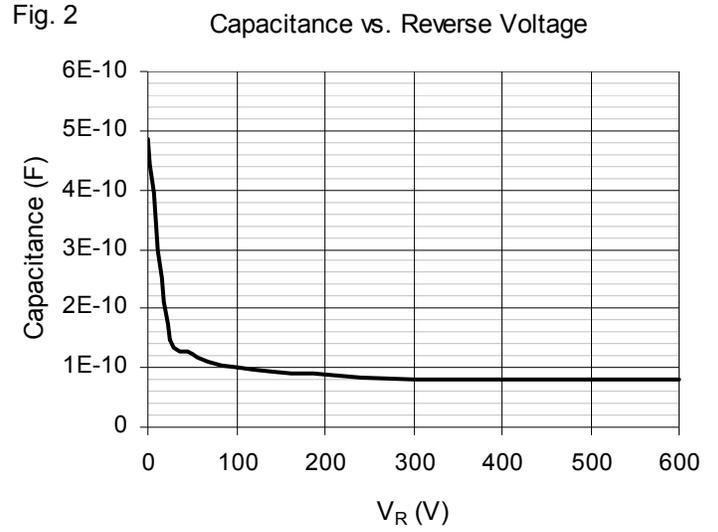
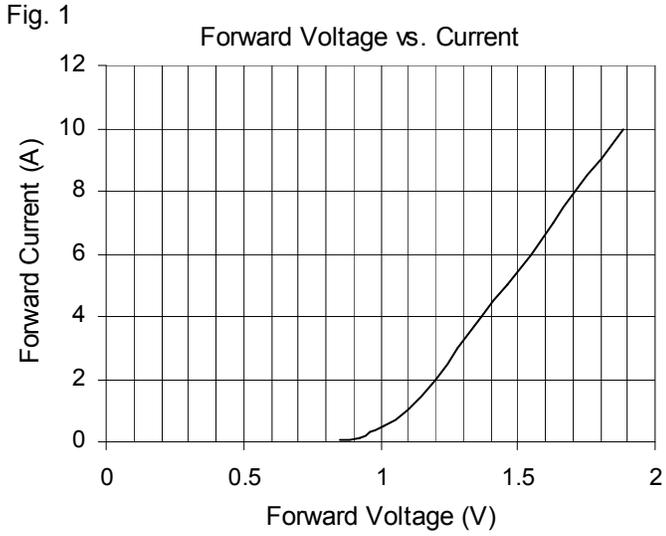


Fig. 6 Package Diagram

